# **Electronic Supplementary Information for**

### 2 "Substrate Effect on Charging of Electrified Graphene/water Interfaces"

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#### 6 S1. Charge density on graphene

7 We use Raman spectroscopy to independently determine the graphene Fermi level, and thereby its charge carrier density  $\binom{n_g}{r}$  from the Raman G-band frequency shift.<sup>1,2</sup> The Fermi level in graphene  $\binom{E_F}{r}$  changes with the density of 8 the charge carriers via  $E_F = \hbar |v_F| \sqrt{\pi n_g}$ , where  $v_F (= 1.1 \times 10^{-6} \, m s^{-1})$  is the Fermi velocity in monolayer 9 graphene,<sup>3</sup> and  $n_g$  denotes the charge carrier density in graphene. Meanwhile, it has been shown that the G-band 10 Raman frequency shifts linearly as a function of the Fermi level,  $E_F = 21\Delta\omega_g + 75 [meV]$  for electrons and 11  $E_F = -18\Delta\omega_g - 83 \ [meV]$  for holes. Surface charge density on graphene at various electrochemistry potentials can 12 therefore be determined via Raman spectral analysis of the G-band Raman frequency shifts. The Raman spectra of the 13 graphene electrode when changing the applied potentials are shown in Fig. S1, corresponding  $\sigma_g$  as a function of 14 applied potentials is shown in Fig. 1e. 15 16



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#### 21 S2. Self-consistent theory

According to self-consistent theory, the charges  $(n_s = \sigma_s/e)$  on the substrate could induce a residual charged

23 impurity concentration in graphene  $(^{n_g})$ , which is given by;<sup>4,5</sup>

 $n_{s} = \frac{n_{g}}{\left[2r_{s}^{2}C_{0}^{RPA}\left(r_{s}, a = 4d\sqrt{\pi n_{g}}\right)\right]}, \#(S1)$   $r_{s} = 2a^{2}/\hbar m (c_{s} + c_{s}) C_{s}^{RPA}$ 

2 where  $r_s = 2e^2/\hbar v_F(\varepsilon_1 + \varepsilon_2)$ ,  $C_0^{RPA}$  is the correlation function from the random phase approximation (RPA), and d3 (~1 nm) is the average distance from the charged impurity to graphene.  $\varepsilon_1$  and  $\varepsilon_2$  are the dielectric constants of SiO<sub>2</sub> 4 and electrolyte solution, respectively, which gives a value of  $r_s$  of 0.05.  $C_0^{RPA}$  can be calculated according to ref.<sup>5</sup>. 5 Solving the Eq. S1, we obtain  $n_g' = 5 \times 10^{11} cm^{-2}$  corresponding to 0.8 mC/m<sup>2</sup> for  $\sigma_s = 100$  mC/m<sup>2</sup>.

#### 6 S3. Interfacial acid-base equilibria and determination of local pH

7 We used the Henderson-Hasselbalch equation<sup>6</sup> to describe the relationship between the local pH and the PA 8 under the assumption that the PA is proportional to the density of the charged species on the SiO<sub>2</sub> surface. The fitting 9 yields two pKa values of ~4.3 and ~9.0 (Fig. S2), consistent with the previous studies that the SiO<sub>2</sub> surface has two 10 distinct types of silanol surface groups with  $pK_a$  values of ~4.5 and ~8.5 respectively.<sup>7–9</sup>

11 The fitting equation allows us to infer the local pH using the PA of the  $Im(\chi^{(2)})$  spectra measured at various 12 applied potentials.<sup>10</sup> The inferred local pH value is shown in Fig. 2.

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15 Fig. S2. Interfacial acid-base equilibria at the SiO<sub>2</sub>-supported graphene electrode/aqueous electrolyte 16 interface. PA of the H-bonded O-H peak as a function of the solution pH at the SiO<sub>2</sub>-supported graphene 17 electrode/aqueous electrolyte interface. We used 10 mM NaClO<sub>4</sub>. The red dashed line is the fitting results using 18 the Henderson-Hasselbalch equation.<sup>10</sup>

#### 19 S4. Tafel plots

Tafel plots can quantify the HER kinetics. The plots are shown in Fig.S3. The Tafel slope in the potential range of -0.23 V to -0.63 V is 571 mV/decade (dashed line), which is a very large value compared to a metal electrode like Pt.<sup>11</sup> Such a large Tafel slope indicates slow HER kinetics and reflects the low catalytic activity of the graphene electrode.<sup>12</sup> At potentials below -0.63 V, the slope of the Tafel plots increases, suggesting even slower HER kinetics. This explains the saturation of the local pH increase at potentials below -0.63 V. The proton diffusion limits the HERinduced pH increase at the graphene/water interface and, in turn, the pH change at the SiO<sub>2</sub>/water interface.



3 Fig. S3. HER kinetics. a. CV of the SiO<sub>2</sub>-supported graphene electrode. The scan rate is 50 mV/s. We used 10 mM
4 NaClO<sub>4</sub>. For simplicity, only the scan in the negative direction is shown. b. Corresponding Tafel plot.

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